

Provisional Data

Extra Fast Recovery Diode

Type F1600NC120

Development Type No. Fx021NC120

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage, (note 1)	1200	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	1300	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{F(AV)}$	Mean forward current, $T_{sink}=55^{\circ}C$, (note 2)	1326	A
$I_{F(AV)}$	Mean forward current, $T_{sink}=100^{\circ}C$, (note 2)	605	A
$I_{F(AV)}$	Mean forward current, $T_{sink}=100^{\circ}C$, (note 3)	337	A
$I_{F(RMS)}$	Nominal RMS forward current, $T_{sink}=25^{\circ}C$, (note 2)	2673	A
$I_{F(D.C.)}$	D.C. forward current, $T_{sink}=25^{\circ}C$, (note 4)	2186	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=0.6V_{RRM}$, (note 5)	20000	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, (note 5)	22000	A
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{RM}=0.6V_{RRM}$, (note 5)	2.00×10^6	A^2s
I^2t	I^2t capacity for fusing $t_p=10ms$, $V_{RM}\leq 10V$, (note 5)	2.42×10^6	A^2s
T_{HS}	Operating temperature range	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range	-40 to +150	$^{\circ}C$

Notes:-

- 1) De-rating factor of 0.13% per $^{\circ}C$ is applicable for T_j below $25^{\circ}C$.
- 2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
- 3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave, $125^{\circ}C$ T_j initial.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{FM}	Maximum peak forward voltage	-	-	1.55 1.77	$I_{FM}=1000A$ $I_{FM}=1600A$	V
V_0	Threshold voltage	-	-	1.32	Over current range 1326 – 3978A (Note 2)	V
r_s	Slope resistance	-	-	0.268		mΩ
V_{01}	Threshold voltage	-	-	1.373	Over current range 1600 – 4800A	V
r_{s1}	Slope resistance	-	-	0.247		mΩ
V_{FRM}	Maximum forward recovery voltage	-	-	20	$di/dt = 1000A/\mu s$, 25°C	V
V_{FRM}	Maximum forward recovery voltage	-	-	30	$di/dt = 1000A/\mu s$	V
I_{RRM}	Peak reverse current	-	-	275 50	Rated V_{RRM} Rated V_{RRM} , $T_J=25^\circ C$	mA
Q_{rr}	Recovered charge	-	50	-	$I_{FM}=1000A$, $t_p=1000\mu s$, $di/dt=60A/\mu s$, $V_r=50V$ (Note 3)	μC
Q_{ra}	Recovered charge, 50% Chord	-	20	30		μC
I_{rm}	Reverse recovery current	-	35	-		A
t_{rr}	Reverse recovery time, 50% Chord	-	1.0	-		μs
Q_{rr}	Recovered charge	-	700	-	$I_{FM}=1600A$, $t_p=500\mu s$, $di/dt=800A/\mu s$, $V_r=800V$	μC
Q_{ra}	Recovered charge, 50% Chord	-	550	-		μC
I_{rm}	Reverse recovery current	-	480	-		A
t_{rr}	Reverse recovery time, 50% Chord	-	2.3	-		μs
$R_{th(j-hs)}$	Thermal resistance, junction to heatsink	-	-	0.024 0.048	Double side cooled Single side cooled	K/W
F	Mounting force	19	-	26		kN
W_t	Weight	-	510	-		g

Notes:-

- 1) Unless otherwise indicated $T_J=125^\circ C$.
- 2) V_0 and r_s were used to calculate the current ratings illustrated on page one
- 3) Figures 3 to 6 were compiled using these conditions

Notes on Ratings and Characteristics**1.0 Voltage Grade Table**

Voltage Grade	V_{RRM} (V)	V_{RSM} (V)	V_R dc (V)
12	1200	1300	600

2.0 De-rating Factor

A blocking voltage de-rating factor of 0.13% per °C is applicable to this device for T_j below 25°C.

3.0 ABCD Constants

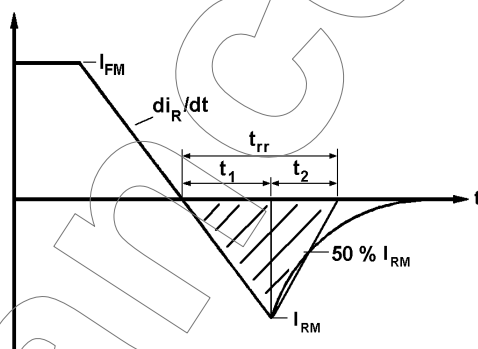
These constants (applicable only over current range of V_F characteristic in Figure 1) are the coefficients of the expression for the forward characteristic given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

where I_F = instantaneous forward current.

4.0 Reverse recovery ratings

- (i) Q_{ra} is based on 50% I_{RM} chord as shown in Fig.(a) below.



- (ii) Q_{rr} is based on a 150μs integration time.

i.e.

$$Q_{rr} = \int_0^{150\mu s} i_{rr} \cdot dt$$

(iii)

$$K \text{ Factor} = \frac{t_1}{t_2}$$

5.0 Reverse Recovery Loss

The following procedure is recommended for use where it is necessary to include reverse recovery loss.

From waveforms of recovery current obtained from a high frequency shunt (see Note 1) and reverse voltage present during recovery, an instantaneous reverse recovery loss waveform must be constructed. Let the area under this waveform be E joules per pulse. A new sink temperature can then be evaluated from:

$$T_{SINK} = T_{J(MAX)} - E \cdot [k + f \cdot R_{th(J-Hs)}]$$

Where $k = 0.2314$ ($^{\circ}\text{C/W}$)/s

E = Area under reverse loss waveform per pulse in joules (W.s.)

f = Rated frequency in Hz at the original sink temperature.

$R_{th(J-Hs)}$ = d.c. thermal resistance ($^{\circ}\text{C/W}$)

The total dissipation is now given by:

$$W_{(tot)} = W_{(original)} + E \cdot f$$

NOTE 1 - Reverse Recovery Loss by Measurement

This device has a low reverse recovered charge and peak reverse recovery current. When measuring the charge, care must be taken to ensure that:

(a) AC coupled devices such as current transformers are not affected by prior passage of high amplitude forward current.

(b) A suitable, polarised, clipping circuit must be connected to the input of the measuring oscilloscope to avoid overloading the internal amplifiers by the relatively high amplitude forward current signal.

(c) Measurement of reverse recovery waveform should be carried out with an appropriate critically damped snubber, connected across diode anode to cathode. The formula used for the calculation of this snubber is shown below:

$$R^2 = 4 \cdot \frac{V_r}{C_s \cdot di/dt}$$

Where: V_r = Commutating source voltage
 C_s = Snubber capacitance
 R = Snubber resistance

6.0 Computer Modelling Parameters

6.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_o + \sqrt{V_o^2 + 4 \cdot ff \cdot r_s \cdot W_{AV}}}{2 \cdot ff \cdot r_s}$$

Where $V_o = 1.32V$, $r_s = 0.268m\Omega$

ff = form factor (normally unity for fast diode applications)

$$W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j(MAX)} - T_{Hs}$$

6.2 Calculation of V_F using ABCD Coefficients

The forward characteristic I_F Vs V_F , on page 6 is represented in two ways;

- the well established V_o and r_s tangent used for rating purposes and
- a set of constants A, B, C, and D forming the coefficients of the representative equation for V_F in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given in this report for hot characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

125°C Coefficients	
A	0.374060321
B	0.08526548
C	6.73844×10^{-5}
D	0.01643

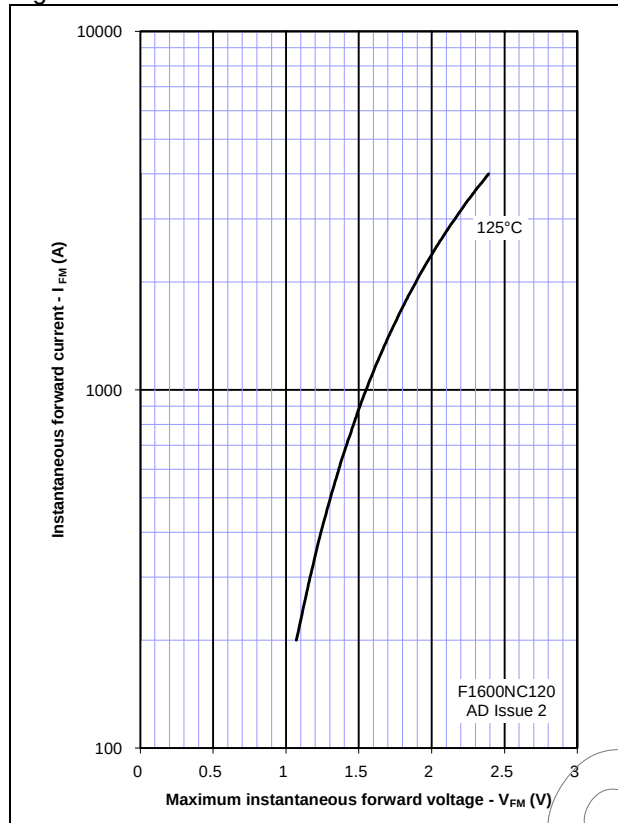
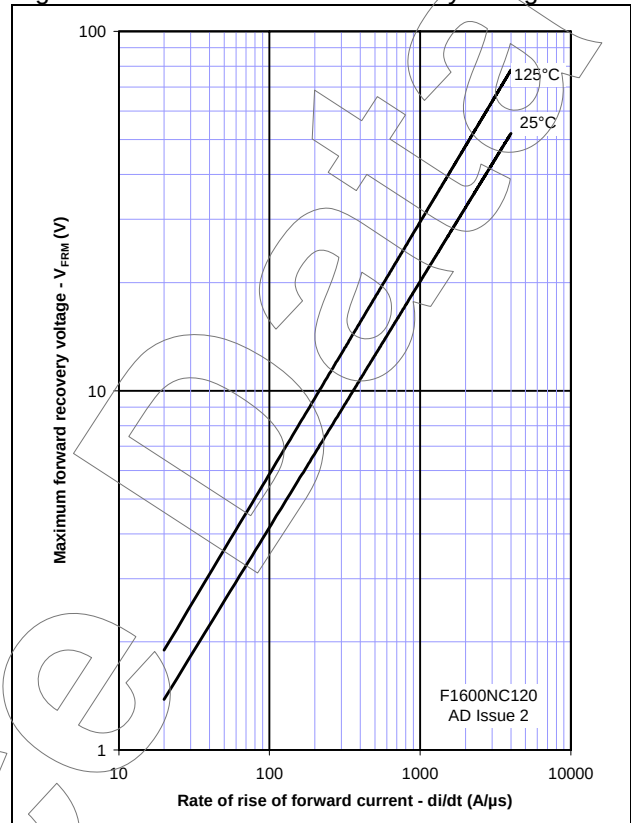
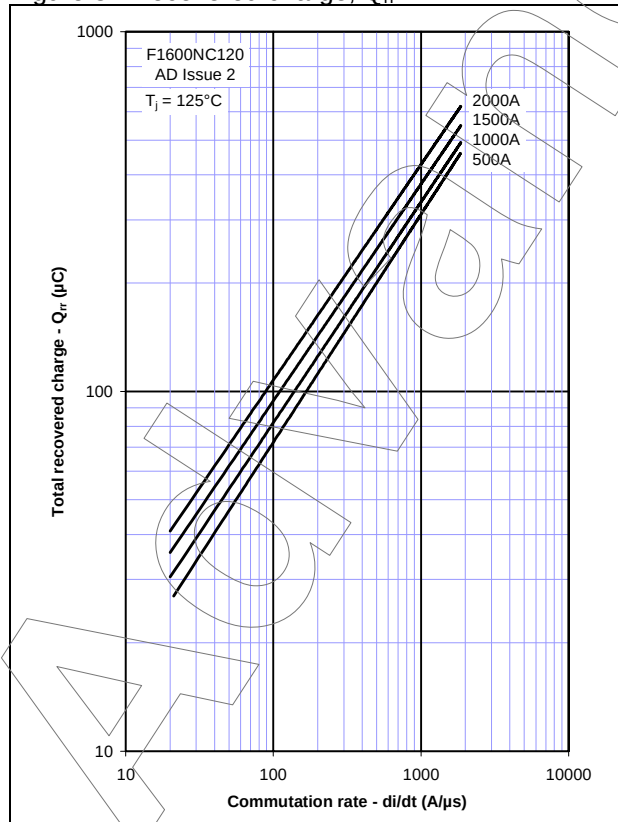
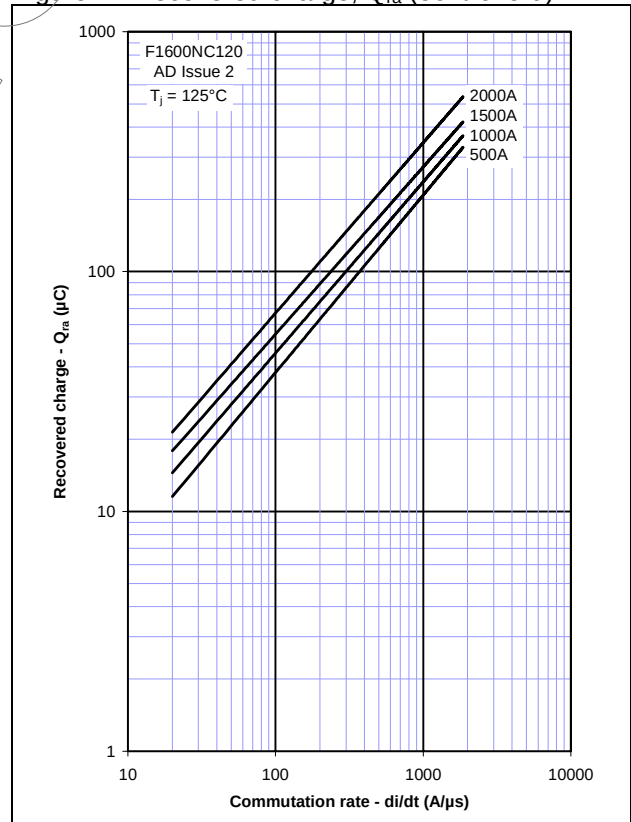
Curves**Figure 1 – Forward characteristics of Limit device****Figure 2 – Maximum forward recovery voltage****Figure 3 - Recovered charge, Q_{rr}** **Figure 4 - Recovered charge, Q_{ra} (50% chord)**

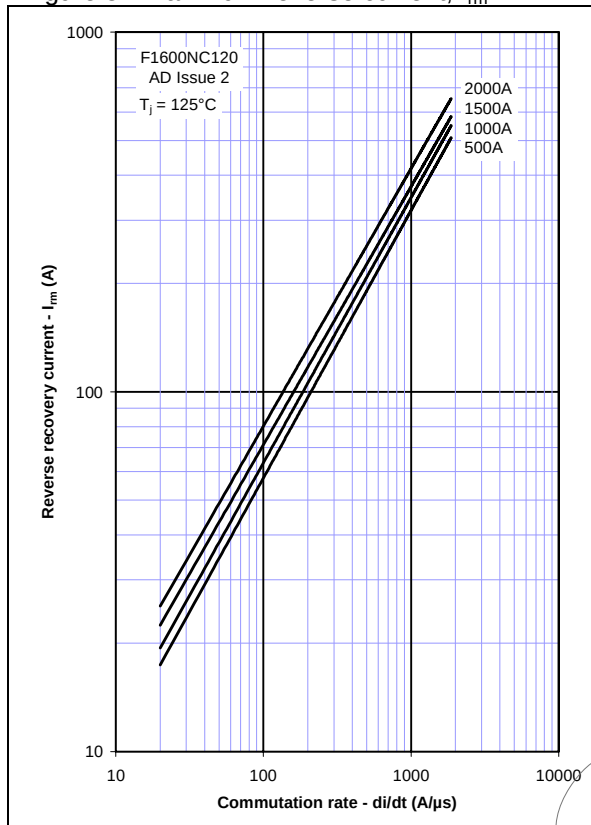
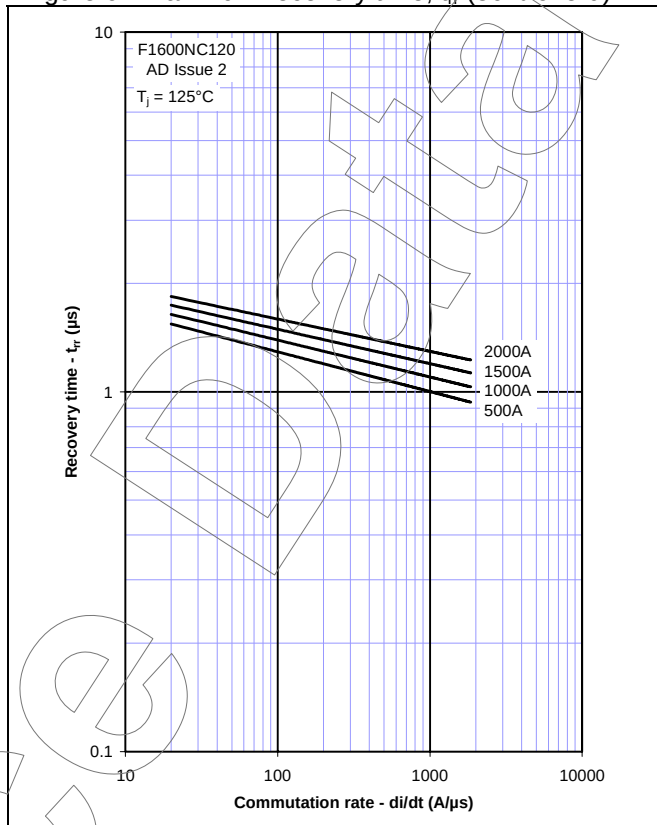
Figure 5 - Maximum reverse current, I_{rm} Figure 6 - Maximum recovery time, t_{rr} (50% chord)

Figure 7 - Reverse recovery energy per pulse

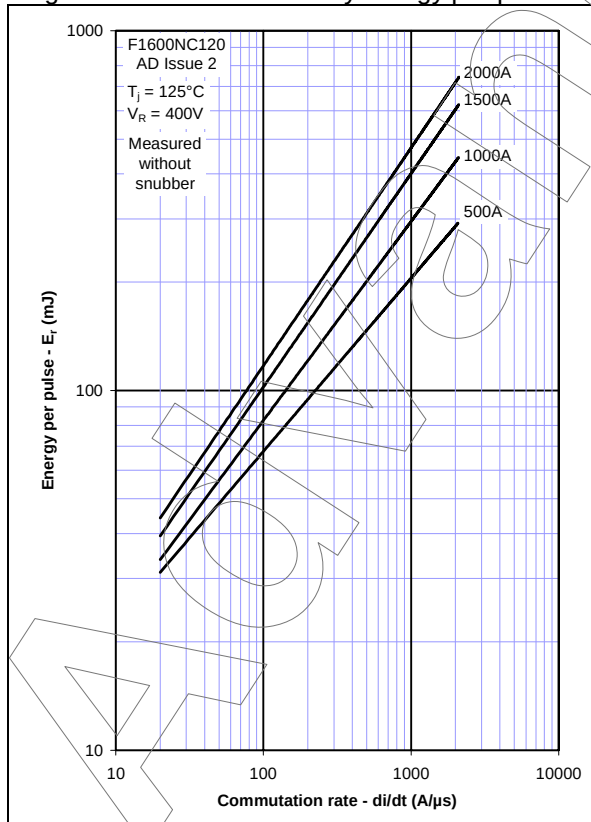


Figure 8 - Sine wave energy per pulse

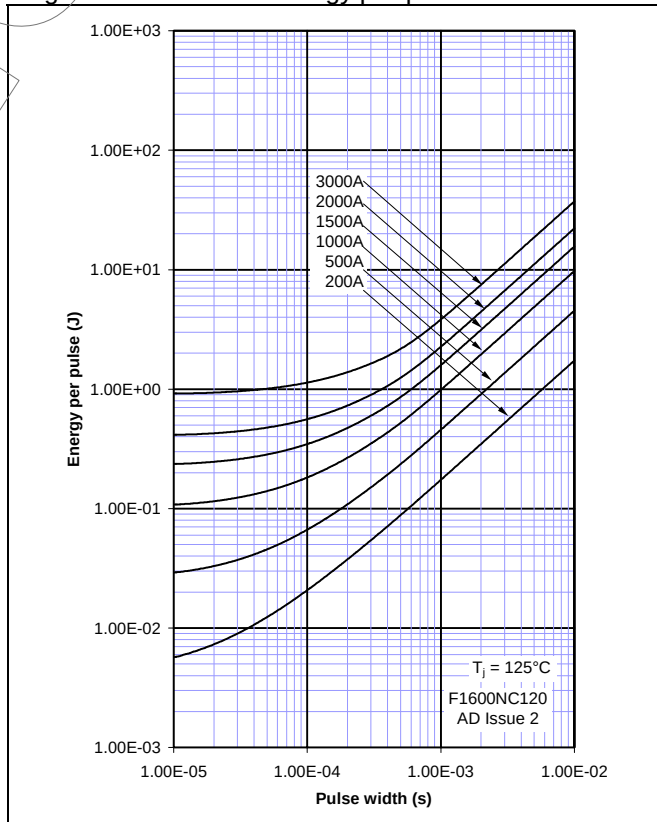


Figure 9 - Sine wave frequency vs. pulse width

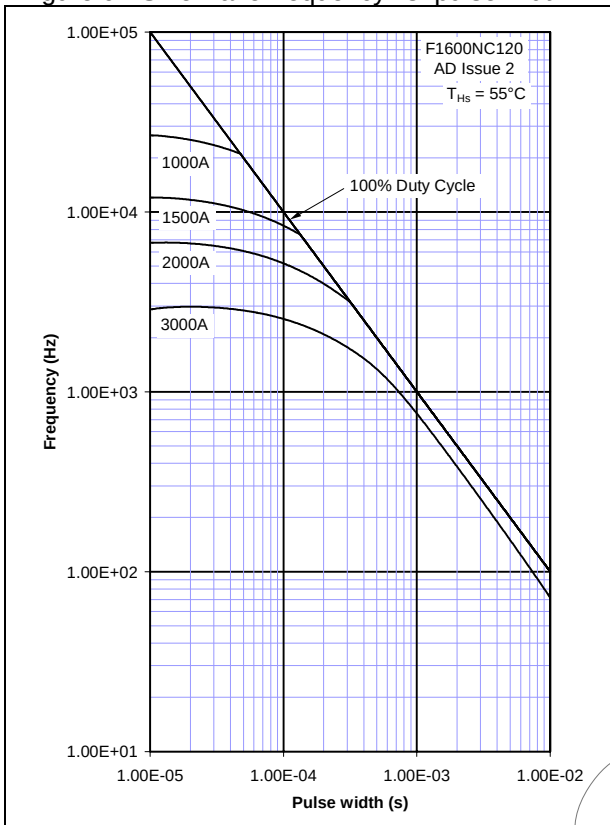


Figure 10 - Sine wave frequency vs. pulse width

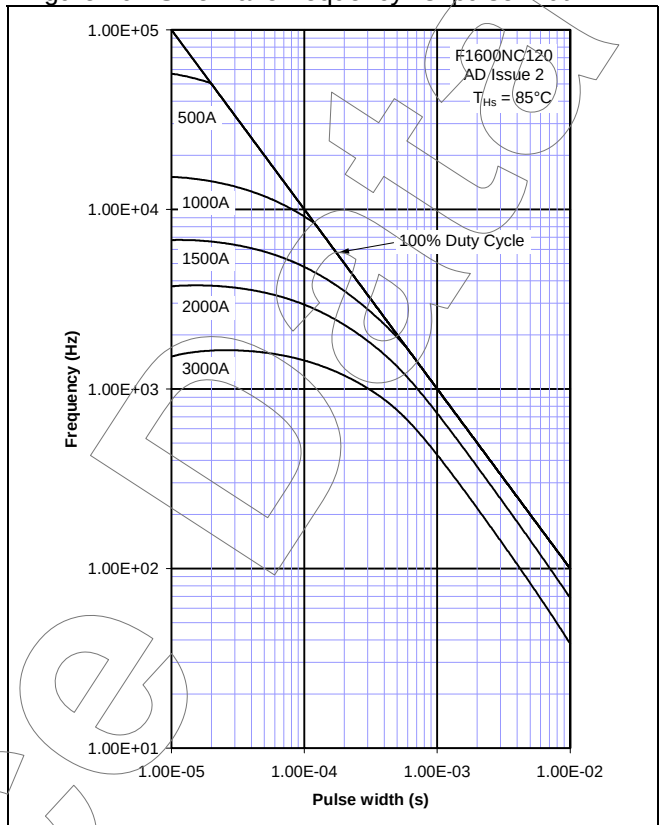


Figure 11 - Square wave energy per pulse

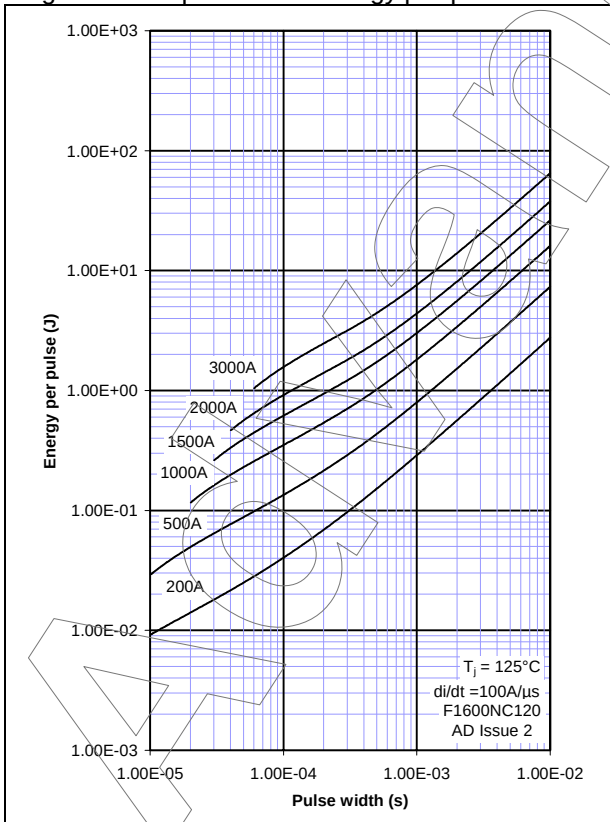


Figure 12 - Square wave energy per pulse

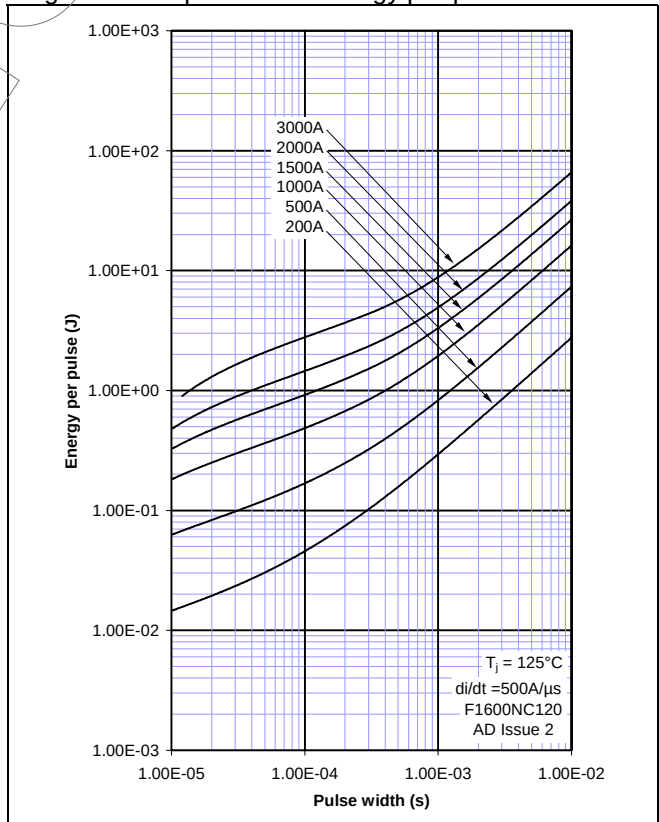


Figure 13 - Square wave frequency vs. pulse width

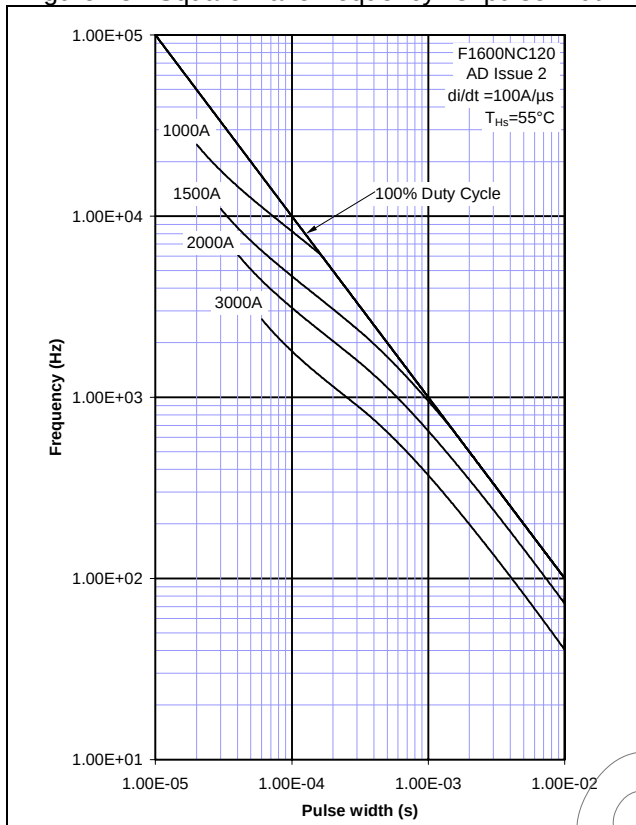


Figure 14 - Square wave frequency vs. pulse width

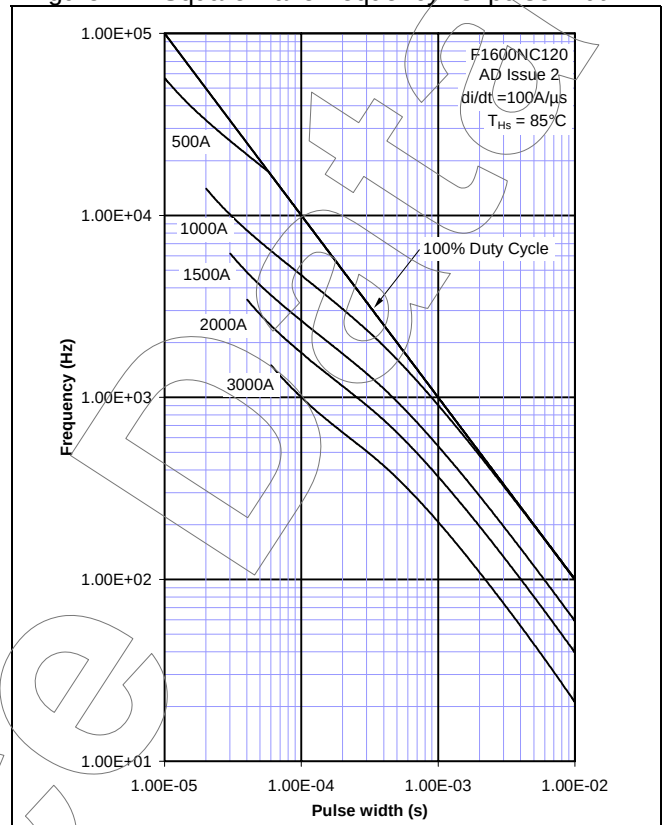


Figure 15 - Square wave frequency vs. pulse width

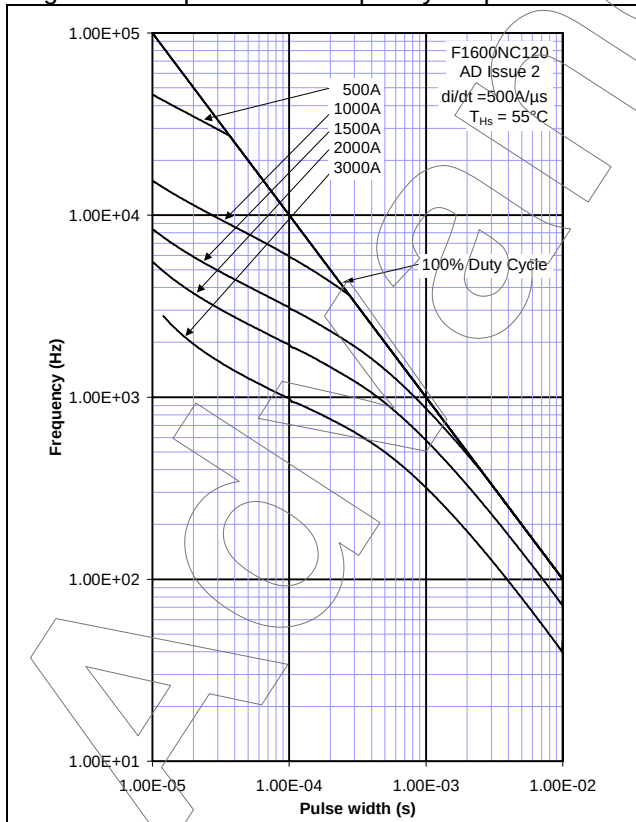


Figure 16 - Square wave frequency vs. pulse width

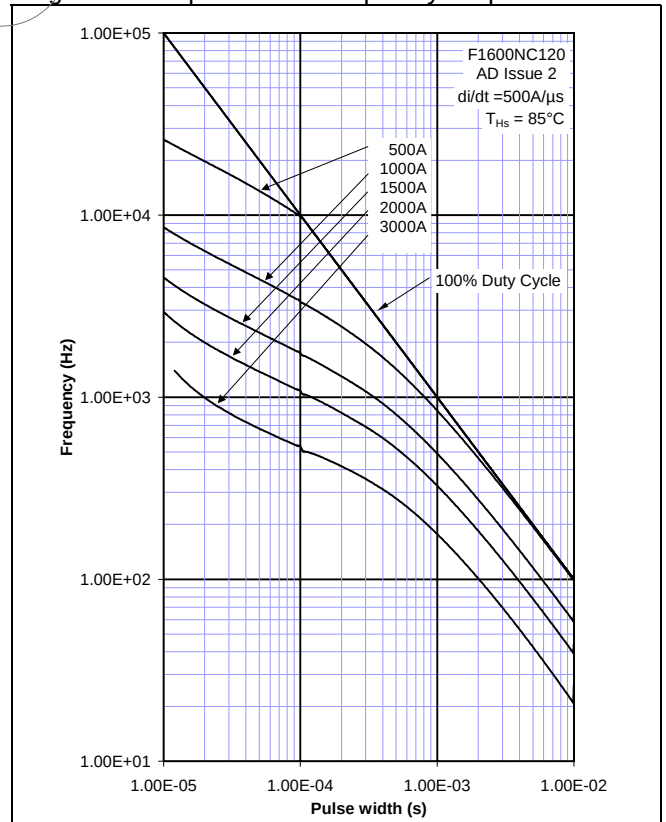


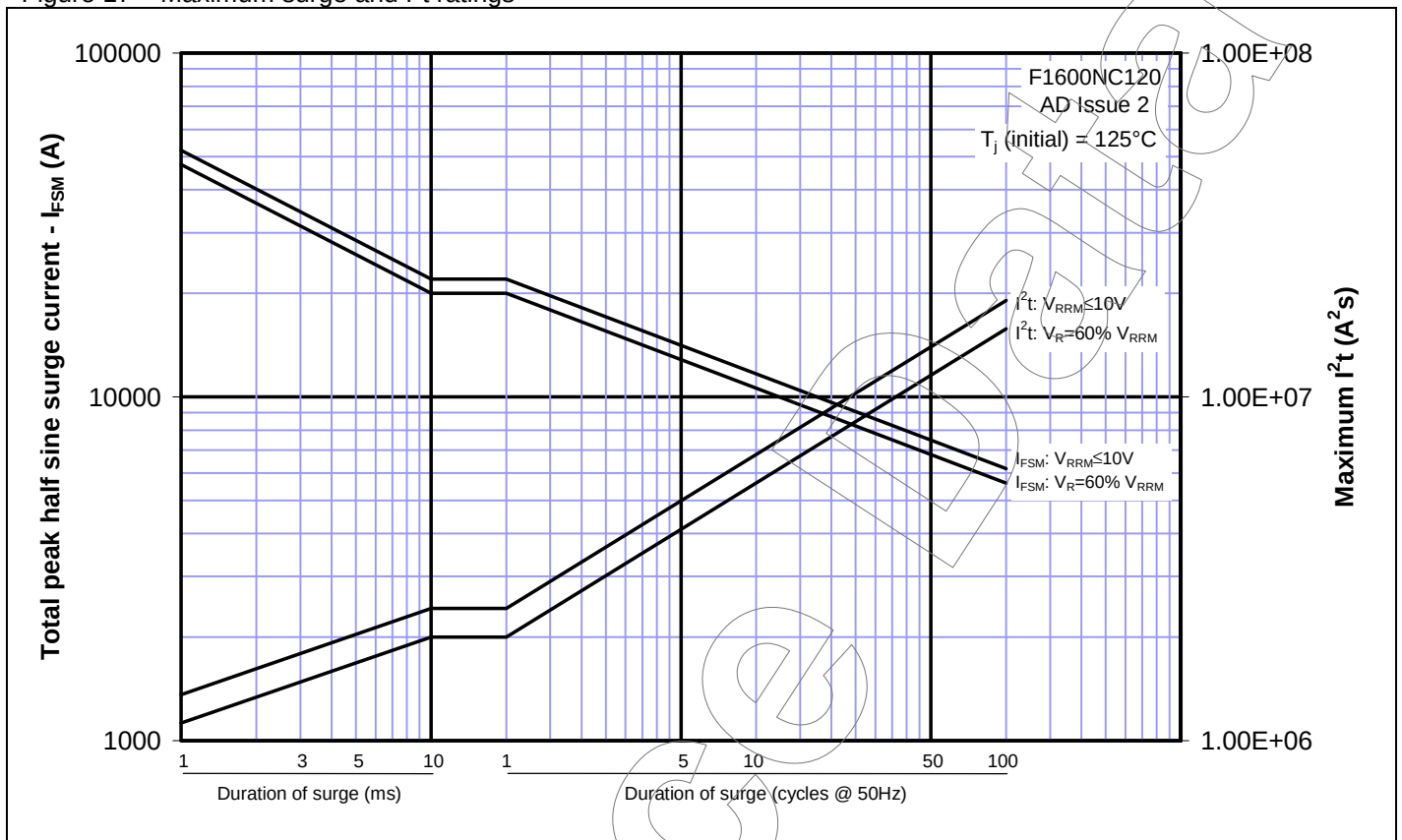
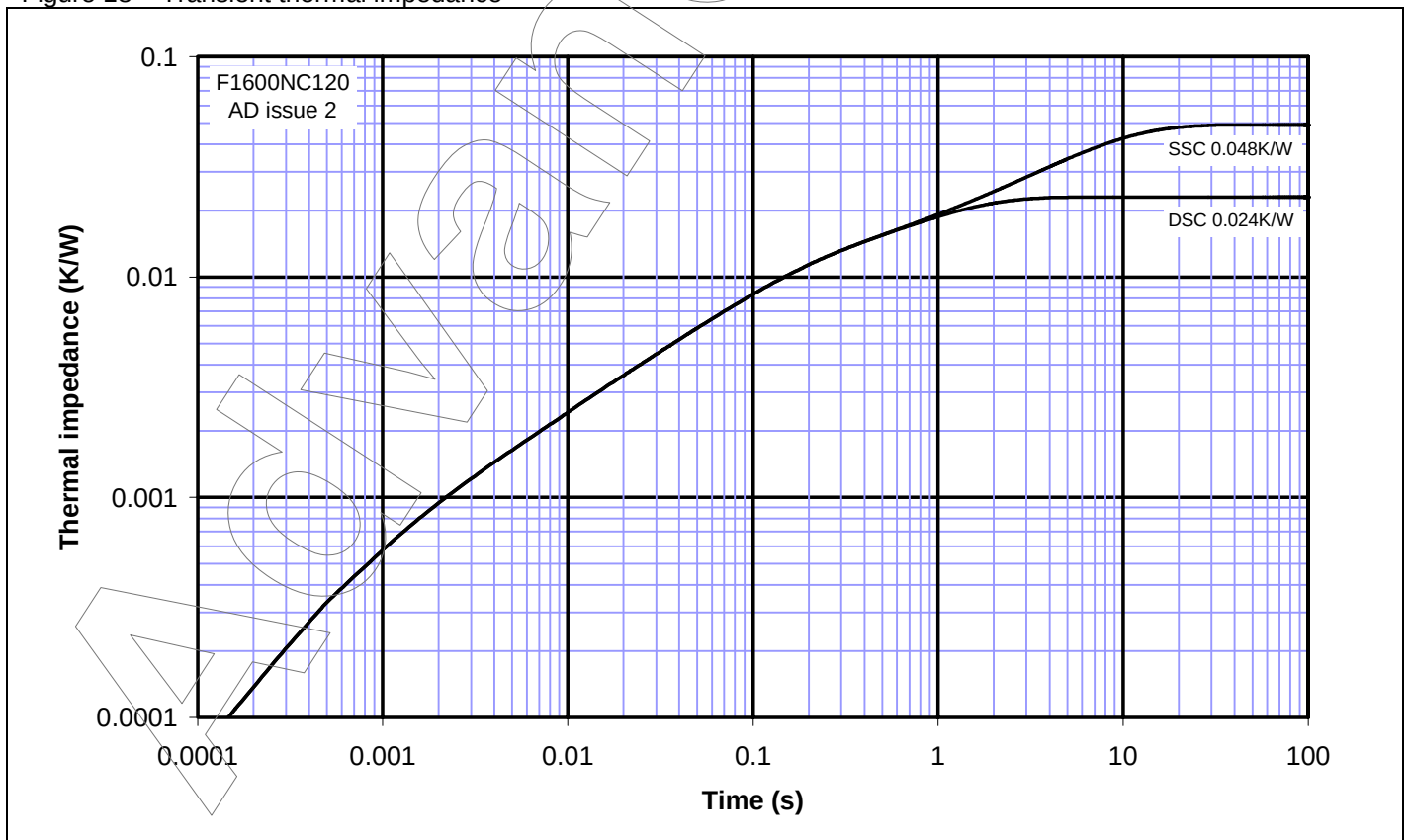
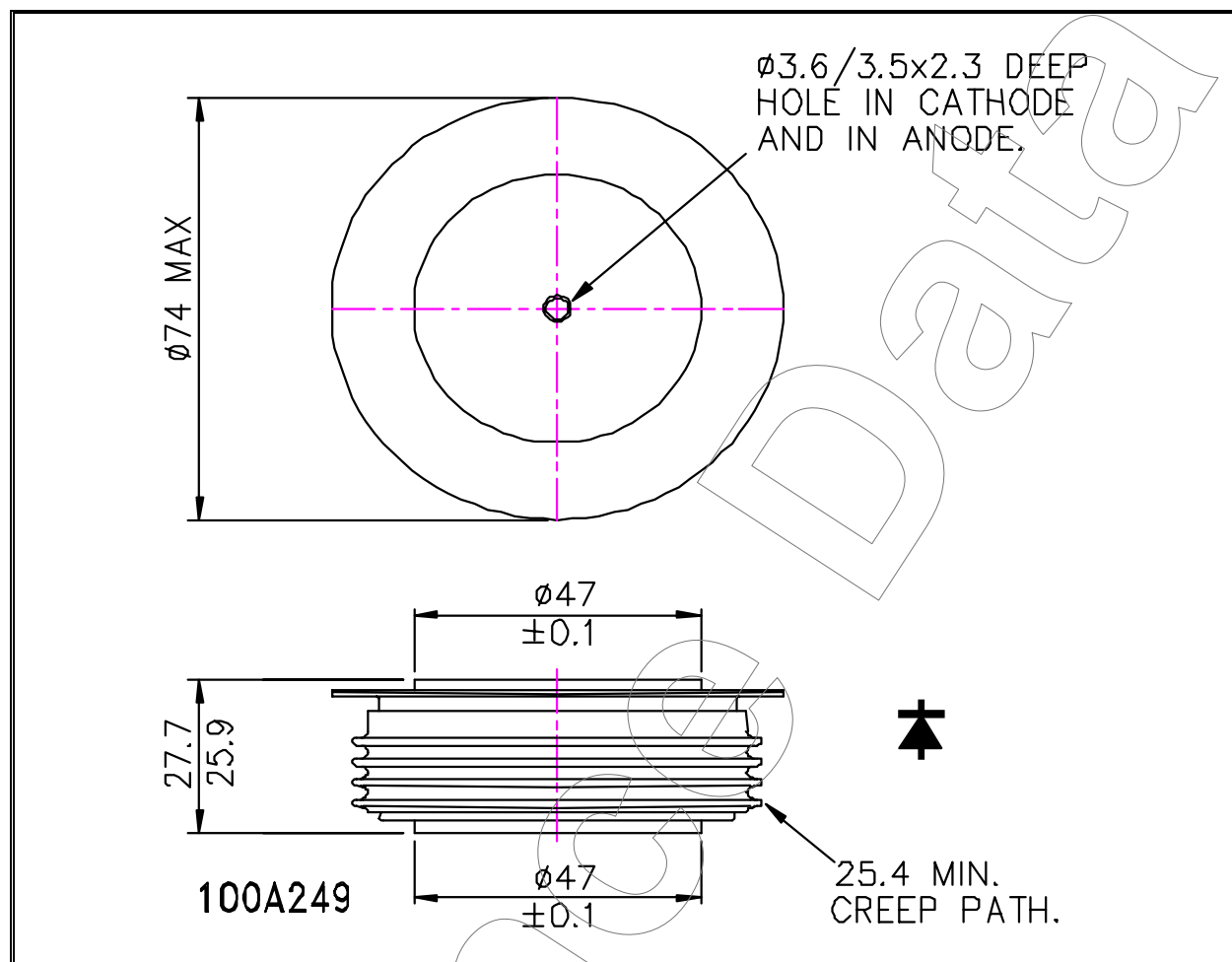
Figure 17 – Maximum surge and I^2t ratings

Figure 18 – Transient thermal impedance



Outline Drawing & Ordering Information**ORDERING INFORMATION**

(Please quote 10 digit code as below)

F1600	NC	◆◆	0
Fixed Type Code	Fixed outline code	Voltage code $V_{DRM}/100$ 12	Fixed code

Order code: F1600NC120 – 1200V V_{RRM} , 26.6mm clamp height capsule.

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 Fax: +49 6206 503-627
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